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ADS7811

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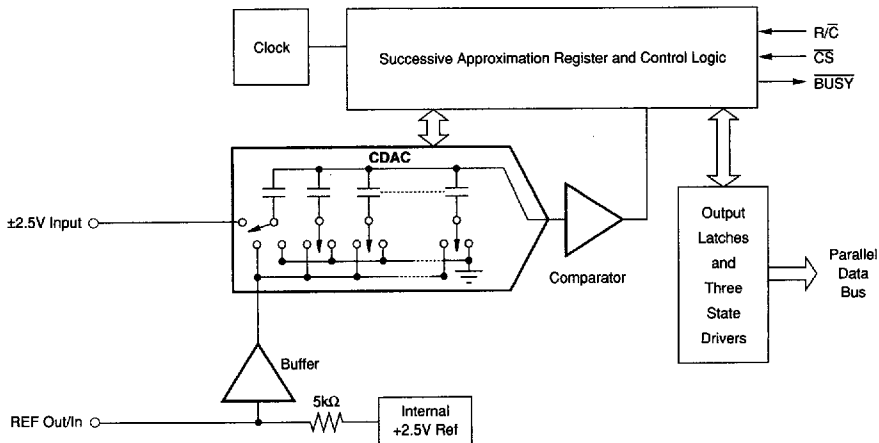
## 16-Bit 250kHz Sampling CMOS ANALOG-to-DIGITAL CONVERTER

### FEATURES

- 250kHz SAMPLING RATE
- $\pm 2.5V$  INPUT RANGE
- COMPLETE WITH S/H, REF, CLOCK, ETC.
- FULL PARALLEL DATA OUTPUT WITH LATCHES
- 28-PIN 0.3" PLASTIC DIP AND SOIC
- 86dB min SINAD WITH 100kHz INPUT
- INL:  $\pm 1.5$  LSB max
- USES INTERNAL OR EXTERNAL REFERENCE
- DNL: 16 Bits "No Missing Codes"

### DESCRIPTION

The ADS7811 is a complete 16-bit sampling analog-to-digital converter using state-of-the-art CMOS structures. It contains a 16-bit capacitor-based SAR A/D with inherent S/H, reference, clock, interface for microprocessor use, and three-state output drivers. The 28-pin ADS7811 is available in a plastic 0.3" DIP and in an SOIC, both fully specified for operation over the industrial  $-25^{\circ}C$  to  $+85^{\circ}C$  range. The ADS7811 is specified at a 250kHz sampling rate, and guaranteed over the full temperature range. A  $\pm 2.5V$  input range allows development of precision systems using only  $\pm 5V$  supplies.



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Or, Call Customer Service at 1-800-548-6132 (USA Only)

# SPECIFICATIONS

At  $T_A = -25^\circ\text{C}$  to  $+85^\circ\text{C}$ ,  $f_S = 250\text{kHz}$ ,  $V_{\text{DIG}} = +V_{\text{ANA}} = +5\text{V} \pm 5\%$ , and  $-V_{\text{ANA}} = -5\text{V} \pm 5\%$ , using internal reference, unless otherwise specified.

PARAMETER	CONDITIONS	ADS7811P, U			ADS7811PB, UB			UNITS	
		MIN	TYP	MAX	MIN	TYP	MAX		
<b>RESOLUTION</b>				16			*	Bits	
<b>ANALOG INPUT</b>									
Voltage Range			$\pm 2.5\text{V}$			*	*	V	
Impedance			100			*	*	$\text{M}\Omega$	
Capacitance			50			*	*	pF	
<b>THROUGHPUT SPEED</b>									
Conversion Cycle	Acquire and Convert			4.0			*	$\mu\text{s}$	
Throughput Rate		250			*		*	kHz	
<b>DC ACCURACY</b>									
Integral Linearity Error		14	$\pm 3$		15	$\pm 1.5$	$\pm 3$	LSB <sup>(1)</sup>	
No Missing Codes			1			*	*	Bits	
Transition Noise <sup>(2)</sup>				$\pm 0.5$		*	$\pm 0.25$	LSB	
Full Scale Error <sup>(3,4)</sup>						*	*	%	
Full Scale Error Drift			$\pm 7$			$\pm 5$	*	$\text{ppm}/^\circ\text{C}$	
Bipolar Zero Error <sup>(3)</sup>				$\pm 10$		*	*	mV	
Bipolar Zero Error Drift			$\pm 2$			*	*	$\text{ppm}/^\circ\text{C}$	
Power Supply Sensitivity ( $V_{\text{DIG}} = V_{\text{ANA}} = V_{\text{D}}$ )	$+4.75\text{V} < V_{\text{D}} < +5.25\text{V}$ , $-5.25\text{V} < -V_{\text{ANA}} < -4.75\text{V}$		$\pm 4$			*	*	LSB	
			$\pm 4$			*	*	LSB	
<b>AC ACCURACY</b>									
Spurious-Free Dynamic Range	$f_{\text{IN}} = 100\text{kHz}$	90			96			$\text{dB}^{(5)}$	
Total Harmonic Distortion	$f_{\text{IN}} = 100\text{kHz}$			-90			-96	$\text{dB}$	
Signal-to-(Noise+Distortion)	$f_{\text{IN}} = 100\text{kHz}$ -60dB Input	84	28		86	30		$\text{dB}$	
Signal-to-Noise	$f_{\text{IN}} = 100\text{kHz}$	84			86	*	*	$\text{dB}$	
Full Power Bandwidth <sup>(6)</sup>			1			*	*	MHz	
<b>SAMPLING DYNAMICS</b>									
Aperture Delay	FS Step		40			*	*	ns	
Transient Response		600				*	*	ns	
Overvoltage Recovery <sup>(7)</sup>		150				*	*	ns	
<b>REFERENCE</b>									
Internal Reference Voltage		2.48	2.5	2.52	*	*	*	V	
Internal Reference Source Current			1		*	*	*	$\mu\text{A}$	
External Reference Voltage Range for Specified Linearity		2.3	2.5	2.7	*	*	*	V	
External Reference Current Drain	$V_{\text{REF}} = +2.5\text{V}$			100			*	$\mu\text{A}$	
<b>DIGITAL INPUTS</b>									
Logic Levels									
$V_{\text{IL}}$		-0.3			*	*	*	V	
$V_{\text{IH}}$		$+2.8$		$+0.8$	*	*	*	V	
$I_{\text{IL}}$				$V_{\text{D}} + 0.3\text{V}$	*	*	*	$\mu\text{A}$	
$I_{\text{IH}}$				$\pm 10$	*	*	*	$\mu\text{A}$	
				$\pm 10$	*	*	*	$\mu\text{A}$	
<b>DIGITAL OUTPUTS</b>									
Data Format					Parallel 16 bits				
Data Coding					Binary Two's Complement				
$V_{\text{OL}}$	$I_{\text{SINK}} = 1.6\text{mA}$ $I_{\text{SOURCE}} = 200\mu\text{A}$ High-Z State, $V_{\text{OUT}} = 0\text{V}$ to $V_{\text{DIG}}$ High-Z State	+4		+0.4	*	*	*	V	
$V_{\text{OH}}$						*	*	*	V
Leakage Current				$\pm 5$		*	*	*	$\mu\text{A}$
Output Capacitance				15			15	pF	
<b>DIGITAL TIMING</b>									
Bus Access Time				65			*	ns	
Bus Relinquish Time				65			*	ns	

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A/D CONVERTERS, DATA ACQUISITION COMPONENTS

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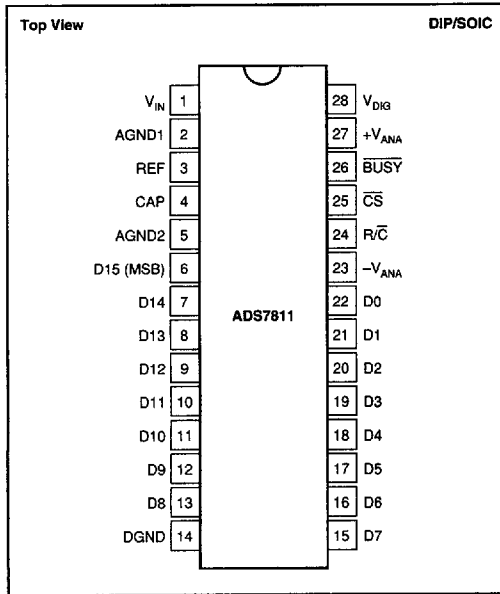
## SPECIFICATIONS (CONT)

At  $T_A = -25^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ,  $f_S = 250\text{kHz}$ ,  $V_{\text{DIG}} = +V_{\text{ANA}} = +5\text{V} \pm 5\%$ , and  $-V_{\text{ANA}} = -5\text{V} \pm 5\%$ , using internal reference, unless otherwise specified.

PARAMETER	CONDITIONS	ADS7811P, U			ADS7811PB, UB			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
<b>POWER SUPPLIES</b>								
Specified Performance					*	*	*	V
$V_{\text{DIG}}$		+4.75	+5	+5.25	*	*	*	V
$+V_{\text{ANA}}$		+4.75	+5	+5.25	*	*	*	V
$-V_{\text{ANA}}$		-5.25	-5	-4.75	*	*	*	V
Power Dissipation	$f_S = 250\text{kHz}$		160	250			*	mW
<b>TEMPERATURE RANGE</b>								
Specified Performance		-25		+85	*		*	$^{\circ}\text{C}$
Storage		-55		+125	*		*	$^{\circ}\text{C}$

NOTES: (1) LSB means Least Significant Bit. For the 16-bit,  $\pm 2.5\text{V}$  input ADS7811, one LSB is  $76\mu\text{V}$ . (2) Typical rms noise at worst case transitions and temperatures. (3) Adjustable to zero with external potentiometer. (4) Full scale error is the worst case of -Full Scale or +Full Scale untrimmed deviation from ideal first and last code transitions, divided by the transition voltage (not divided by the full-scale range) and includes the effect of offset error. (5) All specifications in dB are referred to a full-scale  $\pm 2.5\text{V}$  input. (6) Full-Power Bandwidth defined as Full-Scale input frequency at which Signal-to-(Noise+Distortion) degrades to 60dB, or 10 bits of accuracy. (7) Recovers to specified performance after 2 x FS input overvoltage.

## PIN CONFIGURATION



PIN #	NAME	DESCRIPTION
1	V <sub>IN</sub>	Analog Input. Full-scale input range is ±2.5V.
2	AGND1	Analog Ground. Used internally as ground reference point.
3	REF	Reference Input/Output. Outputs internal reference of +2.5V nominal. Can also be driven by external system reference. In both cases, connect to ground with a 0.1µF ceramic capacitor.
4	CAP	Reference compensation capacitor. 2.2µF tantalum capacitor to ground.
5	AGND2	Analog ground.
6	D15 (MSB)	Data Bit 15. Most Significant Bit (MSB) of conversion results. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
7	D14	Data Bit 14. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
8	D13	Data Bit 13. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
9	D12	Data Bit 12. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
10	D11	Data Bit 11. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
11	D10	Data Bit 10. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
12	D9	Data Bit 9. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
13	D8	Data Bit 8. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
14	DGND	Digital Ground.
15	D7	Data Bit 7. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
16	D6	Data Bit 6. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
17	D5	Data Bit 5. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
18	D4	Data Bit 4. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
19	D3	Data Bit 3. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
20	D2	Data Bit 2. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
21	D1	Data Bit 1. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
22	D0 (LSB)	Data Bit 0. Least Significant Bit (LSB) of conversion results. Hi-Z state when $\overline{CS}$ is HIGH, or when $R/\overline{C}$ is LOW.
23	-V <sub>ANA</sub>	Analog negative supply input. Nominally -5V. Decouple to analog ground with 0.1µF ceramic and 10µF tantalum capacitors.
24	R/ $\overline{C}$	Read/convert input. With $\overline{CS}$ LOW, a falling edge on $R/\overline{C}$ puts the internal sample/hold into the hold state and starts a conversion. With $\overline{CS}$ LOW, a rising edge on $R/\overline{C}$ enables the output data bits.
25	$\overline{CS}$	Chip select. Internally OR'd with $R/\overline{C}$ . With $R/\overline{C}$ LOW, a falling edge on $\overline{CS}$ will initiate a conversion. With $R/\overline{C}$ HIGH, a falling edge on $\overline{CS}$ will enable the output data bits.
26	$\overline{BUSY}$	Busy output. Falls when a conversion is started, and remains LOW until the conversion is completed and the data is latched into the output register. With $\overline{CS}$ LOW and $R/\overline{C}$ HIGH, output data will be valid when $\overline{BUSY}$ rises, so that the rising edge can be used to latch the data. $\overline{CS}$ or $R/\overline{C}$ must be HIGH when $\overline{BUSY}$ rises or another conversion will start without time for signal acquisition.
27	+V <sub>ANA</sub>	Analog positive supply input. Nominally +5V. Connect directly to pin 28. Decouple to ground with 0.1µF ceramic and 10µF tantalum capacitors.
28	V <sub>DIG</sub>	Digital supply input. Nominally +5V. Connect directly to pin 27. Decouple to digital ground with 0.1µF ceramic and 10µF tantalum capacitors.

TABLE I. Pin Assignments.